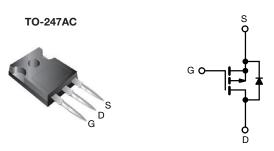


Power MOSFET



P-Channel MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	-100		
R _{DS(on)} (Ω)	V _{GS} = -10 V 0.20		
Q _g (max.) (nC)	61		
Q _{gs} (nC)	14		
Q _{gd} (nC)	29		
Configuration	Single		

FEATURES

- Dynamic dV/dt rating
- · Repetitive avalanche rated
- P-channel
- Isolated central mounting hole
- 175 °C operating temperature
- · Fast switching
- · Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mouting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP9140PbF

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-100	.,
Gate-source voltage		V_{GS}	± 20	V
Continuous drain current	V_{GS} at - 10 V $T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 100 ^{\circ}\text{C}$	L	-21	
Continuous drain current	$T_C = 100 ^{\circ}$ C	l _D	-15	Α
Pulsed drain current ^a		I _{DM}	-84	
Linear derating factor		1.2	W/°C	
Single pulse avalanche energy ^b	E _{AS}	960	mJ	
Repetitive avalanche current a		I _{AR}	-21	А
Repetitive avalanche energy a		E _{AR}	18	mJ
Maximum power dissipation $T_C = 25 ^{\circ}C$		P _D	180	W
Peak diode recovery dV/dt c	dV/dt	-5.5	V/ns	
Operating junction and storage temperature range	T _J , T _{stg}	-5 to +175	°C	
Soldering recommendations (peak temperature) for 10 s			300 d	
Mounting Torque 6-32 or M3 screw			10	lbf ⋅ in
Mounting Torque	0-32 of M3 screw		1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11) b. $V_{DD}=$ 25 V, starting $T_J=25$ °C, L = 3.3 mH, $R_g=25$ Ω , $I_{AS}=$ 21 A (see fig. 12) c. $I_{SD}\leq$ 21 A, dI/dt \leq 200 A/ μ s, $V_{DD}\leq$ V_{DS} , $T_J\leq$ 175 °C d. 1.6 mm from case



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	
Case-to-sink, flat, greased surface	R _{thCS}	0.24	-	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.83	

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 0$	-250 μA	-100		-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	5 °C, I _D = -1 mA	-	-0.087	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D =$	-250 μA	-2.0	-	-4.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = -100 V, V		-	-	-100	μA
	.033		_S = 0 V, T _J = 150 °C	-	-	-500	μ., .
Drain-source on-state resistance	R _{DS(on)}	$V_{GS} = -10 \text{ V}$	I _D = - 13 A ^b	-	-	0.20	Ω
Forward transconductance	9 _{fs}	$V_{DS} = -50 \text{ V}, I_D$	= - 13 A ^b	6.2	-	-	S
Dynamic							
Input capacitance	C _{iss}	$V_{GS} = 0 V$		-	1400	-	
Output capacitance	C _{oss}	$V_{DS} = -25 \text{ V},$		-	590	-	рF
Reverse transfer capacitance	C _{rss}	f = 1.0 MHz, se	e fig. 5	-	140	-	
Total gate charge	Qg			-	-	61	
Gate-source charge	Q _{gs}	V _{GS} = -10 V	$V_{GS} = -10 \text{ V}$ $I_D = -19 \text{ A}, V_{DS} = -80 \text{ V},$ see fig. 6 and 13 b		-	14	nC
Gate-drain charge	Q _{gd}	See fig. 0 and 13		-	-	29	1
Turn-on delay time	t _{d(on)}			-	16	-	
Rise time	t _r	V _{DD} = -	50 V, I _D = -19 A,	-	73	-]
Turn-off delay time	t _{d(off)}	$R_g = 9.1 \Omega$, $R_D = 2.4 \Omega$, see fig. 10 b		-	34	-	ns
Fall time	t _f			-	57	-	1
Internal drain inductance	L _D	Between lead,	D	-	5.0	-	
Internal source inductance	L _S		6 mm (0.25") from package and center of		13	-	nH
Drain-Source Body Diode Characteristic	cs						
Continuous source-drain diode current	I _S	MOSFET symb	ol ol	-	-	- 21	
Pulsed diode forward current ^a	I _{SM}	showing the integral reverse p - n junction diode		-	-	- 84	А
Body diode voltage	V _{SD}	T _J = 25 °C, I _S =	- 21 A, V _{GS} = 0 V ^b	-	-	- 5.0	V
Body diode reverse recovery time	t _{rr}			-	130	260	ns
Body diode reverse recovery charge	Q _{rr}	$T_J = 25 ^{\circ}\text{C}, I_F = -19 \text{A}, dI/dt = 100 \text{A/}\mu\text{s}^{\text{b}}$		-	0.35	0.70	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on		ie domin	ated by I	- and I -/	

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width \leq 300 µs; duty cycle \leq 2 %.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

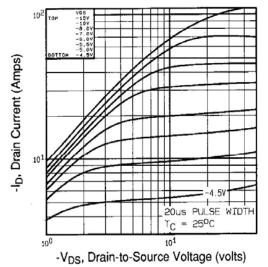


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

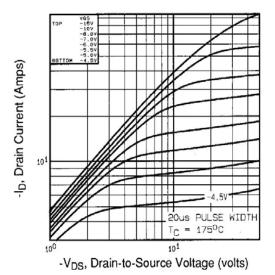


Fig. 2 - Typical Output Characteristics, $T_C = 175$ °C

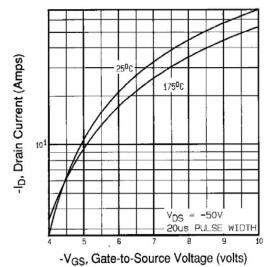


Fig. 3 - Typical Transfer Characteristics

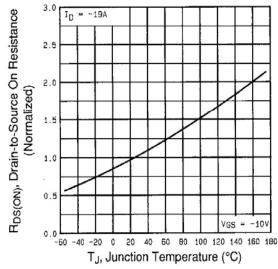


Fig. 4 - Normalized On-Resistance vs. Temperature



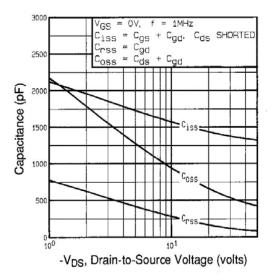


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

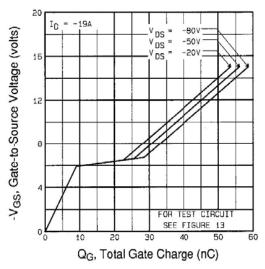


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

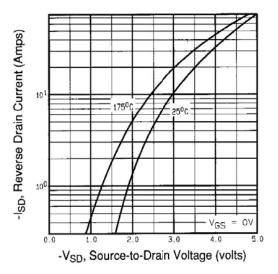


Fig. 7 - Typical Source-Drain Diode Forward Voltage

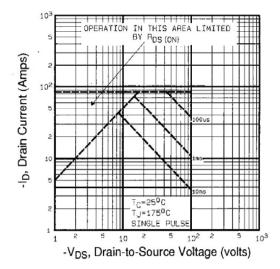


Fig. 8 - Maximum Safe Operating Area



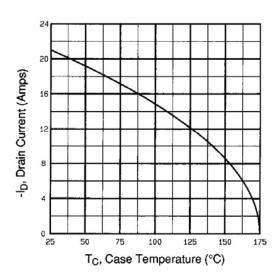


Fig. 9 - Maximum Drain Current vs. Case Temperature

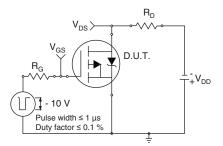


Fig. 10 - Switching Time Test Circuit

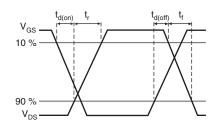


Fig. 11 - Switching Time Waveforms

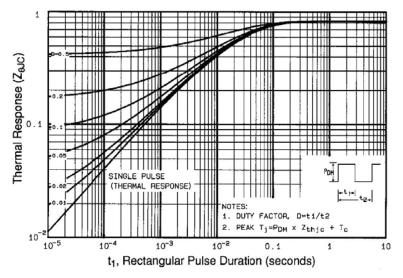


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



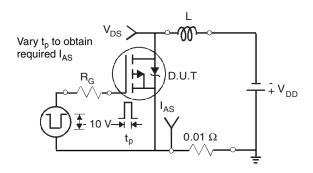


Fig. 13 - Unclamped Inductive Test Circuit

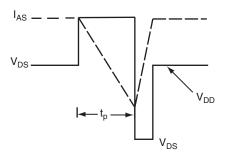


Fig. 14 - Unclamped Inductive Waveforms

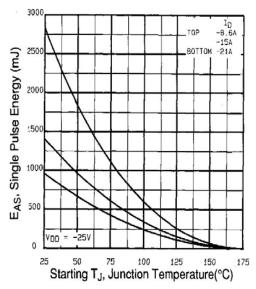


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

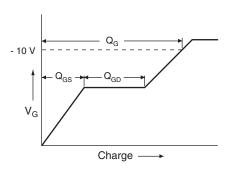


Fig. 16 - Basic Gate Charge Waveform

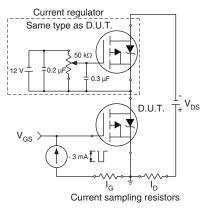
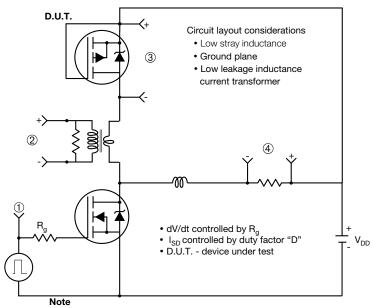


Fig. 17 - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



• Compliment N-Channel of D.U.T. for driver

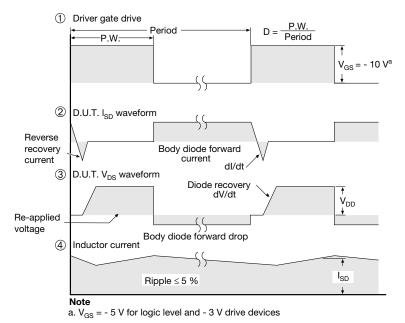


Fig. 18 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91238.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.2	54	
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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